# Lei Liao

## List of Publications by Citations



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|---|---|---|---|
| 126 papers | 5,448 citations | 35 h-index | 72 g-index |
| 139 ext. papers | 6,782 ext. citations | 9.8 avg, IF | 5.73 L-index |

| # | Paper | IF | Citations |
|---|---|---|---|
| 126 | Approaching the Schottky-Mott limit in van der Waals metal-semiconductor junctions. *Nature*, **2018**, 557, 696-700 | 50.4 | 766 |
| 125 | Two-dimensional antimonene single crystals grown by van der Waals epitaxy. *Nature Communications*, **2016**, 7, 13352 | 17.4 | 633 |
| 124 | Ultrafast growth of single-crystal graphene assisted by a continuous oxygen supply. *Nature Nanotechnology*, **2016**, 11, 930-935 | 28.7 | 277 |
| 123 | Direct growth of SnO2nanorod array electrodes for lithium-ion batteries. *Journal of Materials Chemistry*, **2009**, 19, 1859 | | 263 |
| 122 | Monolayer atomic crystal molecular superlattices. *Nature*, **2018**, 555, 231-236 | 50.4 | 220 |
| 121 | High-kappa oxide nanoribbons as gate dielectrics for high mobility top-gated graphene transistors. *Proceedings of the National Academy of Sciences of the United States of America*, **2010**, 107, 6711-5 | 11.5 | 161 |
| 120 | Plasmon-driven reaction controlled by the number of graphene layers and localized surface plasmon distribution during optical excitation. *Light: Science and Applications*, **2015**, 4, e342-e342 | 16.7 | 154 |
| 119 | From Copper Nanocrystalline to CuO Nanoneedle Array: Synthesis, Growth Mechanism, and Properties. *Journal of Physical Chemistry C*, **2007**, 111, 5050-5056 | 3.8 | 153 |
| 118 | Sub-100 nm channel length graphene transistors. *Nano Letters*, **2010**, 10, 3952-6 | 11.5 | 145 |
| 117 | Top-gated graphene nanoribbon transistors with ultrathin high-k dielectrics. *Nano Letters*, **2010**, 10, 1917-21 | 11.5 | 141 |
| 116 | Recent Advances in Optoelectronic Devices Based on 2D Materials and Their Heterostructures. *Advanced Optical Materials*, **2019**, 7, 1800441 | 8.1 | 132 |
| 115 | Confining Cation Injection to Enhance CBRAM Performance by Nanopore Graphene Layer. *Small*, **2017**, 13, 1603948 | 11 | 113 |
| 114 | Direct Vapor Growth of Perovskite CsPbBr Nanoplate Electroluminescence Devices. *ACS Nano*, **2017**, 11, 9869-9876 | 16.7 | 96 |
| 113 | Multiwall boron carbonitride/carbon nanotube junction and its rectification behavior. *Journal of the American Chemical Society*, **2007**, 129, 9562-3 | 16.4 | 83 |
| 112 | Efficient strain modulation of 2D materials via polymer encapsulation. *Nature Communications*, **2020**, 11, 1151 | 17.4 | 81 |
| 111 | 200 GHz Maximum Oscillation Frequency in CVD Graphene Radio Frequency Transistors. *ACS Applied Materials & Interfaces*, **2016**, 8, 25645-25649 | 9.5 | 80 |
| 110 | Ultrafine Graphene Nanomesh with Large On/Off Ratio for High-Performance Flexible Biosensors. *Advanced Functional Materials*, **2017**, 27, 1604096 | 15.6 | 78 |

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|---|---|---|---|
| 109 | Single-layer graphene on Al2O3/Si substrate: better contrast and higher performance of graphene transistors. *Nanotechnology*, **2010**, 21, 015705 | 3.4 | 78 |
| 108 | Possible absence of critical thickness and size effect in ultrathin perovskite ferroelectric films. *Nature Communications*, **2017**, 8, 15549 | 17.4 | 74 |
| 107 | Enhancing Performance of a GaAs/AlGaAs/GaAs Nanowire Photodetector Based on the Two-Dimensional Electron-Hole Tube Structure. *Nano Letters*, **2020**, 20, 2654-2659 | 11.5 | 74 |
| 106 | Van der Waals epitaxial growth of air-stable CrSe nanosheets with thickness-tunable magnetic order. *Nature Materials*, **2021**, 20, 818-825 | 27 | 68 |
| 105 | Doping-free complementary WSe circuit via van der Waals metal integration. *Nature Communications*, **2020**, 11, 1866 | 17.4 | 68 |
| 104 | High-Performance Near-Infrared Photodetectors Based on p-Type SnX (X = S, Se) Nanowires Grown via Chemical Vapor Deposition. *ACS Nano*, **2018**, 12, 7239-7245 | 16.7 | 62 |
| 103 | MoS Negative-Capacitance Field-Effect Transistors with Subthreshold Swing below the Physics Limit. *Advanced Materials*, **2018**, 30, e1800932 | 24 | 61 |
| 102 | Two-dimensional negative capacitance transistor with polyvinylidene fluoride-based ferroelectric polymer gating. *Npj 2D Materials and Applications*, **2017**, 1, | 8.8 | 57 |
| 101 | Flexible Quasi-2D Perovskite/IGZO Phototransistors for Ultrasensitive and Broadband Photodetection. *Advanced Materials*, **2020**, 32, e1907527 | 24 | 54 |
| 100 | Perovskite/Black Phosphorus/MoS Photogate Reversed Photodiodes with Ultrahigh Light On/Off Ratio and Fast Response. *ACS Nano*, **2019**, 13, 4804-4813 | 16.7 | 53 |
| 99 | Integration of High-k Oxide on MoS2 by Using Ozone Pretreatment for High-Performance MoS2 Top-Gated Transistor with Thickness-Dependent Carrier Scattering Investigation. *Small*, **2015**, 11, 5932-8 | 11 | 48 |
| 98 | High-Resolution Tracking Asymmetric Lithium Insertion and Extraction and Local Structure Ordering in SnS2. *Nano Letters*, **2016**, 16, 5582-8 | 11.5 | 48 |
| 97 | Dependence of Ion-Implant-Induced LBIC Novel Characteristic on Excitation Intensity for Long-Wavelength HgCdTe-Based Photovoltaic Infrared Detector Pixel Arrays. *IEEE Journal of Selected Topics in Quantum Electronics*, **2013**, 19, 1-7 | 3.8 | 43 |
| 96 | Highly Flexible and Bright Electroluminescent Devices Based on Ag Nanowire Electrodes and Top-Emission Structure. *Advanced Electronic Materials*, **2017**, 3, 1600535 | 6.4 | 42 |
| 95 | Recent Advances in Low-Dimensional Heterojunction-Based Tunnel Field Effect Transistors. *Advanced Electronic Materials*, **2019**, 5, 1800569 | 6.4 | 39 |
| 94 | Coaxial-Structured Weavable and Wearable Electroluminescent Fibers. *Advanced Electronic Materials*, **2017**, 3, 1700401 | 6.4 | 38 |
| 93 | Recent Progress on Electrical and Optical Manipulations of Perovskite Photodetectors. *Advanced Science*, **2021**, 8, e2100569 | 13.6 | 37 |
| 92 | Transferred van der Waals metal electrodes for sub-1-nm MoS2 vertical transistors. *Nature Electronics*, **2021**, 4, 342-347 | 28.4 | 36 |

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|---|---|---|---|
| 91 | Large-area, well-ordered, uniform-sized bowtie nanoantenna arrays for surface enhanced Raman scattering substrate with ultra-sensitive detection. *Applied Physics Letters*, **2013**, 103, 041903 | 3.4 | 35 |
| 90 | Photoresponse improvement of mixed-dimensional 1D-2D GaAs photodetectors by incorporating constructive interface states. *Nanoscale*, **2021**, 13, 1086-1092 | 7.7 | 35 |
| 89 | Ferroelectric polymer tuned two dimensional layered MoTe2 photodetector. *RSC Advances*, **2016**, 6, 87416-87421 | 3.7 | 34 |
| 88 | Impact of Thickness on Contact Issues for Pinning Effect in Black Phosphorus Field-Effect Transistors. *Advanced Functional Materials*, **2018**, 28, 1801398 | 15.6 | 32 |
| 87 | Improved performance of HgCdTe infrared detector focal plane arrays by modulating light field based on photonic crystal structure. *Journal of Applied Physics*, **2014**, 115, 184504 | 2.5 | 29 |
| 86 | Defect Self-Compensation for High-Mobility Bilayer InGaZnO/In2O3 Thin-Film Transistor. *Advanced Electronic Materials*, **2019**, 5, 1900125 | 6.4 | 27 |
| 85 | Vapor phase growth of two-dimensional PdSe2 nanosheets for high-photoresponsivity near-infrared photodetectors. *Nano Research*, **2020**, 13, 2091-2097 | 10 | 26 |
| 84 | Enhanced Reliability of InGaZnO Thin-Film Transistors Through Design of Dual Passivation Layers. *IEEE Transactions on Electron Devices*, **2018**, 65, 2844-2849 | 2.9 | 26 |
| 83 | High performance top-gated ferroelectric field effect transistors based on two-dimensional ZnO nanosheets. *Applied Physics Letters*, **2017**, 110, 043505 | 3.4 | 24 |
| 82 | Broadband photodetection of 2D Bi2O2Se/MoSe2 heterostructure. *Journal of Materials Science*, **2019**, 54, 14742-14751 | 4.3 | 24 |
| 81 | Improving Charge Mobility of Polymer Transistors by Judicious Choice of the Molecular Weight of Insulating Polymer Additive. *Journal of Physical Chemistry C*, **2016**, 120, 17282-17289 | 3.8 | 23 |
| 80 | Doping High-Mobility Donor–Acceptor Copolymer Semiconductors with an Organic Salt for High-Performance Thermoelectric Materials. *Advanced Electronic Materials*, **2020**, 6, 1900945 | 6.4 | 22 |
| 79 | High on/off ratio black phosphorus based memristor with ultra-thin phosphorus oxide layer. *Applied Physics Letters*, **2019**, 115, 193503 | 3.4 | 22 |
| 78 | Rational design of Al/2D perovskite heterostructure dielectric for high performance MoS phototransistors. *Nature Communications*, **2020**, 11, 4266 | 17.4 | 21 |
| 77 | Manganese(ii) enhanced fluorescent nitrogen-doped graphene quantum dots: a facile and efficient synthesis and their applications for bioimaging and detection of Hg ions.. *RSC Advances*, **2018**, 8, 5902-5911 | 3.7 | 20 |
| 76 | Micro/Nanosized Nontraditional Evaporated Structures Based on Closely Packed Monolayer Binary Colloidal Crystals and Their Fine Structure Enhanced Properties. *Journal of Physical Chemistry C*, **2014**, 118, 20521-20528 | 3.8 | 20 |
| 75 | High-Mobility Solution-Processed Amorphous Indium Zinc $\hbox{Oxide/In}_{2}\hbox{O}_{3}$ Nanocrystal Hybrid Thin-Film Transistor. *IEEE Electron Device Letters*, **2013**, 34, 72-74 | 4.4 | 20 |
| 74 | Design of Highly Stable Tungsten-Doped IZO Thin-Film Transistors With Enhanced Performance. *IEEE Transactions on Electron Devices*, **2018**, 65, 1018-1022 | 2.9 | 19 |

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|---|---|---|---|
| 73 | Modulating the threshold voltage of oxide nanowire field-effect transistors by a Ga+ ion beam. *Nano Research*, **2014**, 7, 1691-1698 | 10 | 19 |
| 72 | A high energy output nanogenerator based on reduced graphene oxide. *Nanoscale*, **2015**, 7, 18147-51 | 7.7 | 18 |
| 71 | An Electrically Controlled Wavelength-Tunable Nanoribbon Laser. *ACS Nano*, **2020**, 14, 3397-3404 | 16.7 | 17 |
| 70 | Interface Engineering via MoS2 Insertion Layer for Improving Resistive Switching of Conductive-Bridging Random Access Memory. *Advanced Electronic Materials*, **2019**, 5, 1800747 | 6.4 | 16 |
| 69 | The photovoltaic and photoconductive photodetector based on GeSe/2D semiconductor van der Waals heterostructure. *Applied Physics Letters*, **2020**, 116, 141101 | 3.4 | 16 |
| 68 | Understanding hydrogen and nitrogen doping on active defects in amorphous In-Ga-Zn-O thin film transistors. *Applied Physics Letters*, **2018**, 112, 253504 | 3.4 | 15 |
| 67 | Positive Shift in Threshold Voltage Induced by CuO and NiOx Gate in AlGaN/GaN HEMTs. *IEEE Transactions on Electron Devices*, **2017**, 64, 3139-3144 | 2.9 | 14 |
| 66 | Atomic mechanism of strong interactions at the graphene/sapphire interface. *Nature Communications*, **2019**, 10, 5013 | 17.4 | 13 |
| 65 | High mobility amorphous InGaZnO thin film transistor with single wall carbon nanotubes enhanced-current path. *Applied Physics Letters*, **2013**, 103, 223108 | 3.4 | 13 |
| 64 | Hollow MgO Nanotube Arrays by Using ZnO Nanorods as Templates. *European Journal of Inorganic Chemistry*, **2008**, 2008, 2727-2732 | 2.3 | 13 |
| 63 | Efficient Gate Modulation in a Screening-Engineered MoS/Single-Walled Carbon Nanotube Network Heterojunction Vertical Field-Effect Transistor. *ACS Applied Materials & Interfaces*, **2019**, 11, 25516-25523 | 9.5 | 12 |
| 62 | Effect of Backbone Fluorine and Chlorine Substitution on Charge-Transport Properties of Naphthalenediimide-Based Polymer Semiconductors. *Advanced Electronic Materials*, **2020**, 6, 1901241 | 6.4 | 12 |
| 61 | Possible Luttinger liquid behavior of edge transport in monolayer transition metal dichalcogenide crystals. *Nature Communications*, **2020**, 11, 659 | 17.4 | 12 |
| 60 | Down-Scalable and Ultra-fast Memristors with Ultra-high Density Three-Dimensional Arrays of Perovskite Quantum Wires. *Nano Letters*, **2021**, 21, 5036-5044 | 11.5 | 11 |
| 59 | High Voltage Gain WSe2 Complementary Compact Inverter With Buried Gate for Local Doping. *IEEE Electron Device Letters*, **2020**, 41, 944-947 | 4.4 | 10 |
| 58 | Polarization-Resolved Broadband MoS2/Black Phosphorus/MoS2 Optoelectronic Memory with Ultralong Retention Time and Ultrahigh Switching Ratio. *Advanced Functional Materials*, **2021**, 31, 2100781 | 15.6 | 10 |
| 57 | Reconfigurable electronics by disassembling and reassembling van der Waals heterostructures. *Nature Communications*, **2021**, 12, 1825 | 17.4 | 10 |
| 56 | Microfluidic solution-processed organic and perovskite nanowires fabricated for field-effect transistors and photodetectors. *Journal of Materials Chemistry C*, **2020**, 8, 2353-2362 | 7.1 | 9 |

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|---|---|---|---|
| 55 | Pulsed Laser Deposition Assisted van der Waals Epitaxial Large Area Quasi-2D ZnO Single-Crystal Plates on Fluorophlogopite Mica. *Advanced Materials Interfaces*, **2019**, 6, 1901156 | 4.6 | 9 |
| 54 | Prediction of Stable and High-Performance Charge Transport in Zigzag Tellurene Nanoribbons. *IEEE Transactions on Electron Devices*, **2019**, 66, 2365-2369 | 2.9 | 8 |
| 53 | Nanowires: Anomalous and Highly Efficient InAs Nanowire Phototransistors Based on Majority Carrier Transport at Room Temperature (Adv. Mater. 48/2014). *Advanced Materials*, **2014**, 26, 8232-8232 | 24 | 8 |
| 52 | Impact of hydrogen dopant incorporation on InGaZnO, ZnO and InO thin film transistors. *Physical Chemistry Chemical Physics*, **2020**, 22, 1591-1597 | 3.6 | 8 |
| 51 | Tunable Electrical Properties in High-Valent Transition-Metal-Doped ZnO Thin-Film Transistors. *IEEE Electron Device Letters*, **2014**, 35, 759-761 | 4.4 | 7 |
| 50 | Next-generation machine vision systems incorporating two-dimensional materials: Progress and perspectives. *Informa□□Materi□y*, **2022**, 4, | 23.1 | 7 |
| 49 | Strain Effect Enhanced Ultrasensitive MoS Nanoscroll Avalanche Photodetector. *Journal of Physical Chemistry Letters*, **2020**, 11, 4490-4497 | 6.4 | 6 |
| 48 | Ladder-like metal oxide nanowires: Synthesis, electrical transport, and enhanced light absorption properties. *Nano Research*, **2014**, 7, 272-283 | 10 | 6 |
| 47 | Synergistic effect of V/N codoping by ion implantation on the electronic and optical properties of TiO2. *Journal of Applied Physics*, **2014**, 115, 143106 | 2.5 | 6 |
| 46 | InGaZnO Tunnel and Junction Transistors Based on Vertically Stacked Black Phosphorus/InGaZnO Heterojunctions. *Advanced Electronic Materials*, **2020**, 6, 2000291 | 6.4 | 6 |
| 45 | Toward Unusual-High Hole Mobility of p-Channel Field-Effect-Transistors. *Small*, **2021**, 17, e2102323 | 11 | 6 |
| 44 | Correlation of Molecular Structure and Charge Transport Properties: A Case Study in Naphthalenediimide□Based Copolymer Semiconductors. *Advanced Electronic Materials*, **2018**, 4, 1800203 | 6.4 | 6 |
| 43 | Photodetectors: Ultrasensitive and Broadband MoS2 Photodetector Driven by Ferroelectrics (Adv. Mater. 42/2015). *Advanced Materials*, **2015**, 27, 6538-6538 | 24 | 5 |
| 42 | Van der Waals epitaxy of ultrathin crystalline PbTe nanosheets with high near-infrared photoelectric response. *Nano Research*, **2021**, 14, 1955-1960 | 10 | 5 |
| 41 | Dry Exfoliation of Large-Area 2D Monolayer and Heterostructure Arrays. *ACS Nano*, **2021**, | 16.7 | 5 |
| 40 | Ultra-Steep-Slope High-Gain MoS Transistors with Atomic Threshold-Switching Gate.. *Advanced Science*, **2022**, e2104439 | 13.6 | 4 |
| 39 | High-throughput isolation of fetal nucleated red blood cells by multifunctional microsphere-assisted inertial microfluidics. *Biomedical Microdevices*, **2020**, 22, 75 | 3.7 | 4 |
| 38 | High-Resolution Van der Waals Stencil Lithography for 2D□Transistors. *Small*, **2021**, 17, e2101209 | 11 | 4 |

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| 37 | Hysteresis-Free MoSMetal Semiconductor Field-Effect Transistors with van der Waals Schottky Junction. *Nanotechnology*, **2020**, | 3.4 | 4 |
| 36 | Ultimate dielectric scaling of 2D transistors via van der Waals metal integration. *Nano Research*,1 | 10 | 4 |
| 35 | Solution-Processed CsPbBr Quantum Dots/Organic Semiconductor Planar Heterojunctions for High-Performance Photodetectors.. *Advanced Science*, **2022**, e2105856 | 13.6 | 4 |
| 34 | Simultaneous Surface Display and Holography Enabled by Flat Liquid Crystal Elements. *Laser and Photonics Reviews*,2100491 | 8.3 | 4 |
| 33 | Schottky-Contacted WSe2 Hot-Electron Photodetectors with Fast Response and High Sensitivity. *ACS Photonics*, **2022**, 9, 132-137 | 6.3 | 4 |
| 32 | Triblock copolymer-assisted construction of 20 nm-sized ytterbium-doped TiO2 hollow nanostructures for enhanced solar energy utilization efficiency. *Science China Chemistry*, **2015**, 58, 850-857 | 7.9 | 3 |
| 31 | Directly Grown K0.33WO3 Nanosheet Film Electrode for Fast Direct Electron Transfer of Protein. *ChemElectroChem*, **2014**, 1, 463-470 | 4.3 | 3 |
| 30 | Au Nanoarrays: Surface Plasmon-Enhanced Photodetection in Few Layer MoS2 Phototransistors with Au Nanostructure Arrays (Small 20/2015). *Small*, **2015**, 11, 2346-2346 | 11 | 3 |
| 29 | Electrical Properties in Group IV Elements-Doped ZnO Thin-Film Transistors. *Journal of Display Technology*, **2015**, 11, 670-673 | | 3 |
| 28 | Transferred metal gate to 2D semiconductors for sub-1 V operation and near ideal subthreshold slope. *Science Advances*, **2021**, 7, eabf8744 | 14.3 | 3 |
| 27 | Amorphous B-doped graphitic carbon nitride quantum dots with high photoluminescence quantum yield of near 90% and their sensitive detection of Fe2+/Cd2+. *Science China Materials*,1 | 7.1 | 3 |
| 26 | Strain-Plasmonic Coupled Broadband Photodetector Based on Monolayer MoS.. *Small*, **2022**, e2107104 | 11 | 3 |
| 25 | Photodetectors: High-Responsivity Graphene/InAs Nanowire Heterojunction Near-Infrared Photodetectors with Distinct Photocurrent On/Off Ratios (Small 8/2015). *Small*, **2015**, 11, 890-890 | 11 | 2 |
| 24 | Transparent megahertz circuits from solution-processed composite thin films. *Nanoscale*, **2016**, 8, 7978-83 | 7.7 | 2 |
| 23 | Comprehensive insights into effect of van der Waals contact on carbon nanotube network field-effect transistors. *Applied Physics Letters*, **2019**, 115, 173503 | 3.4 | 2 |
| 22 | MoS2 Homojunctions Transistors Enabled by Dimension Tailoring Strategy. *Advanced Electronic Materials*, **2021**, 7, 2100703 | 6.4 | 2 |
| 21 | Doping of Sn-based two-dimensional perovskite semiconductor for high-performance field-effect transistors and thermoelectric devices.. *IScience*, **2022**, 25, 104109 | 6.1 | 2 |
| 20 | Tuning the Electrical Performance of 2D Perovskite Field-Effect Transistors by Forming Organic Semiconductor/Perovskite van der Waals Heterojunctions. *Advanced Electronic Materials*,2200148 | 6.4 | 2 |

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|---|---|---|---|
| 19 | Hydrogen Annealing Effect on the Magnetic Properties of ZnCoO/MoS2 Hybrid. *Journal of Superconductivity and Novel Magnetism*, **2018**, 31, 1241-1245 | 1.5 | 1 |
| 18 | Comment on "Metal Semiconductor Field-Effect Transistor with MoS2/Conducting NiOx van der Waals Schottky Interface for Intrinsic High Mobility and Photoswitching Speed". *ACS Nano*, **2016**, 10, 1714-5 | 16.7 | 1 |
| 17 | Low-Power, High-Sensitivity Temperature Sensor Based on Ultrathin SOI Lateral p-i-n Gated Diode. *IEEE Transactions on Electron Devices*, **2019**, 66, 4001-4007 | 2.9 | 1 |
| 16 | More Recent Advances in One-Dimensional Metal Oxide Nanostructures: Optical and Optoelectronic Applications **2013**, 359-379 | | 1 |
| 15 | Graphene: Confining Cation Injection to Enhance CBRAM Performance by Nanopore Graphene Layer (Small 35/2017). *Small*, **2017**, 13, | 11 | 1 |
| 14 | Black phosphorus field effect transistors stable in harsh conditions via surface engineering. *Applied Physics Letters*, **2020**, 117, 111602 | 3.4 | 1 |
| 13 | High-Performance WSe2 n-Type Field-Effect Transistors Enabled by InOx Damage-Free Doping. *IEEE Electron Device Letters*, **2021**, 1-1 | 4.4 | 1 |
| 12 | Origin of low-temperature negative transconductance in multilayer MoS2 transistors. *Applied Physics Letters*, **2021**, 119, 043502 | 3.4 | 1 |
| 11 | Non-Linear Output-Conductance Function for Robust Analysis of Two-Dimensional Transistors. *IEEE Electron Device Letters*, **2021**, 42, 94-97 | 4.4 | 1 |
| 10 | Schottky-Contacted High-Performance GaSb Nanowires Photodetectors Enabled by Lead-Free All-Inorganic Perovskites Decoration.. *Small*, **2022**, e2200415 | 11 | 1 |
| 9 | Realization of Ultra-Scaled MoS2 Vertical Diodes via Double-Side Electrodes Lamination. *Nano Letters*, | 11.5 | 1 |
| 8 | Solution-Processed Quantum-Dots Light-Emitting Transistors With Equivalent Efficiency of Light-Emitting Diodes. *IEEE Transactions on Electron Devices*, **2021**, 1-4 | 2.9 | 0 |
| 7 | Electronic Fluctuation of Graphene Nanoribbon MOSFETs Under a Full Quantum Dynamics Framework. *IEEE Transactions on Electron Devices*, **2021**, 68, 1980-1985 | 2.9 | 0 |
| 6 | Fast Response GaAs Photodetector Based on Constructing Electron Transmission Channel. *Crystals*, **2021**, 11, 1160 | 2.3 | 0 |
| 5 | 51.4: Invited Paper: High Performance Flexible TFTs from Oxide/Carbon Heterostructures. *Digest of Technical Papers SID International Symposium*, **2015**, 46, 775-777 | 0.5 | |
| 4 | Graphene, Nanotube, and NANOWIRE-Based Electronics **2015**, 413-500 | | |
| 3 | High-Current Omega-Shaped Gated MoS2 Transistors. *IEEE Transactions on Electron Devices*, **2022**, 69, 816-819 | 2.9 | |
| 2 | 15.3: Defect Engineering in n-Type Oxide Semiconductor TFTs. *Digest of Technical Papers SID International Symposium*, **2021**, 52, 101-101 | 0.5 | |

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| 1 | 29.3: Invited Paper: Defect Engineering in n-Type Oxide Semiconductor TFTs. *Digest of Technical Papers SID International Symposium*, **2021**, 52, 400-400 | 0.5 |